TRANSISTOR (PNP) **Plastic-Encapsulate Transistor**

FEATURES

Power dissipation

P_{CM} : 0.2W (Tamb=25°C)

Collector current

I_{CM} : -0.1A

Collector-base Voltage

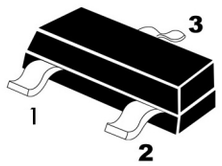
$V_{(BR)CBO}$: -60 V

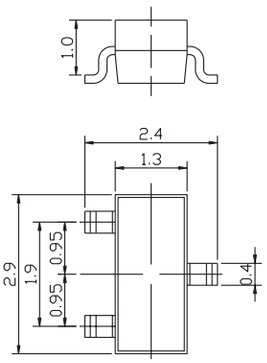
Operating and storage junction temperature range

T_J, T_{stg} : -55°C to +150°C

SOT-23

1. BASE
2. EMITTER
3. COLLECTOR





Unit:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100 μA, I_E=0		-60	V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA, I_B=0		-50	V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100 μA, I_C=0		-5	V
Collector cut-off current	I_{CBO}	V_{CB}=-60V, I_E=0		-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0		-0.1	μA
DC current gain	h_{FE}	V_{CE}=-6V, I_C=-1mA	90	600	
Collector-emitter saturation voltage	V_{CEsat}	I_C=-100mA, I_B=-10mA		-0.3	V
Base-emitter voltage	V_{BE}	I_C=-1mA, V_{CE}=-6V		-0.68	V
Output Capacitance	Cob	V_{CB}=-10V, I_E=0 f=1.0MHZ		4.5	pF
Transition frequency	F_t	V_{CE}=-6V, I_C=-10mA	180		MHZ

CLASSIFICATION OF h_{FE}

Rank	M3	M4	M5	M6	M7
Range	60-120	90-180	135-270	200-400	300-600